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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Dataila	
Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	55
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EPROM Size	-
RAM Size	2.5K x 8
oltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
ata Converters	A/D 12x10b; D/A 2x8b
Scillator Type	Internal
perating Temperature	-40°C ~ 85°C (TA)
Nounting Type	Surface Mount
Package / Case	64-LQFP
upplier Device Package	64-LQFP (14x14)
urchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f212a7sdfa-v2

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Specifications for R8C/2B Group (1) Table 1.3

ltem	Function	Specification
CPU	Central processing	R8C/Tiny series core
	unit	Number of fundamental instructions: 89
		Minimum instruction execution time:
		50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V)
		100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
		200 ns (f(XIN) = 5 MHz, VCC = 2.2 to 5.5 V)
		Multiplier: 16 bits × 16 bits → 32 bits
		 Multiply-accumulate instruction: 16 bits x 16 bits + 32 bits → 32 bits
		Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM	Refer to Table 1.6 Product List for R8C/2B Group.
Power Supply	Voltage detection	Power-on reset
Voltage	circuit	Voltage detection 2
Detection		
I/O Ports	Programmable I/O	Input-only: 2 pins
	ports	CMOS I/O ports: 55, selectable pull-up resistor
		High current drive ports: 8
Clock	Clock generation	3 circuits: XIN clock oscillation circuit (with on-chip feedback resistor),
	circuits	On-chip oscillator (high-speed, low-speed)
		(high-speed on-chip oscillator has a frequency adjustment function),
		XCIN clock oscillation circuit (32 kHz)
		Oscillation stop detection: XIN clock oscillation stop detection function
		• Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16
		Low power consumption modes:
		Standard operating mode (high-speed clock, low-speed clock, high-speed
		on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
		Real-time clock (timer RE)
Interrupts		External: 5 sources, Internal: 23 sources, Software: 4 sources
		Priority levels: 7 levels
Watchdog Tim	er	15 bits × 1 (with prescaler), reset start selectable
Timer	Timer RA	8 bits x 1 (with 8-bit prescaler)
		Timer mode (period timer), pulse output mode (output level inverted every
		period), event counter mode, pulse width measurement mode, pulse period
		measurement mode
	Timer RB	8 bits x 1 (with 8-bit prescaler)
		Timer mode (period timer), programmable waveform generation mode (PWM
		output), programmable one-shot generation mode, programmable wait one-
		shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers)
		Timer mode (input capture function, output compare function), PWM mode
	T DD	(output 3 pins), PWM2 mode (PWM output pin)
	Timer RD	16 bits x 2 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode
		(output 6 pins), reset synchronous PWM mode (output three-phase
		waveforms (6 pins), sawtooth wave modulation), complementary PWM mode
		(output three-phase waveforms (6 pins), triangular wave modulation), PWM3
		mode (PWM output 2 pins with fixed period)
	Timor DE	9 hite v 1
	Timer RE	8 bits x 1 Real-time clock mode (count seconds, minutes, hours, days of week), output
	Timer RE	Real-time clock mode (count seconds, minutes, hours, days of week), output
	Timer RE	

Specifications for R8C/2B Group (2) Table 1.4

Item	Function	Specification
Serial	UARTO, UART1,	Clock synchronous serial I/O/UART x 3
Interface	UART2	
	nous Serial I/O with	1 (shared with I ² C-bus)
Chip Select (S	SU)	
I ² C bus ⁽¹⁾		1 (shared with SSU)
LIN Module		Hardware LIN: 1 (timer RA, UART0)
A/D Converter		10-bit resolution x 12 channels, includes sample and hold function
D/A Converter		8-bit resolution x 2 circuits
Flash Memory		Programming and erasure voltage: VCC = 2.7 to 5.5 V
		Programming and erasure endurance: 10,000 times (data flash)
		1,000 times (program ROM)
		Program security: ROM code protect, ID code check
		Debug functions: On-chip debug, on-board flash rewrite function
Operating Fred	uency/Supply	f(XIN) = 20 MHz (VCC = 3.0 to 5.5 V)
Voltage		f(XIN) = 10 MHz (VCC = 2.7 to 5.5 V) f(XIN) = 5 MHz (VCC = 2.2 to 5.5 V)
Current consur	nntion	12 mA (VCC = 5.0 V, f(XIN) = 20 MHz)
Current consui	прион	5.5 mA (VCC = 3.0 V, f(XIN) = 20 MHz)
		2.1 μ A (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz))
		$0.65 \mu\text{A} (\text{VCC} = 3.0 \text{V}, \text{stop mode})$
Operating Amb	ent Temperature	-20 to 85°C (N version)
		-40 to 85°C (D version) ⁽²⁾
		-20 to 105°C (Y version) ⁽³⁾
Package		64-pin LQFP
		Package code: PLQP0064KB-A (previous code: 64P6Q-A)
		Package code: PLQP0064GA-A (previous code: 64P6U-A)
		64-pin FLGA
		Package code: PTLG0064JA-A (previous code: 64F0G)

- I²C bus is a trademark of Koninklijke Philips Electronics N. V.
 Specify the D version if D version functions are to be used.
 Please contact Renesas Technology sales offices for the Y version.

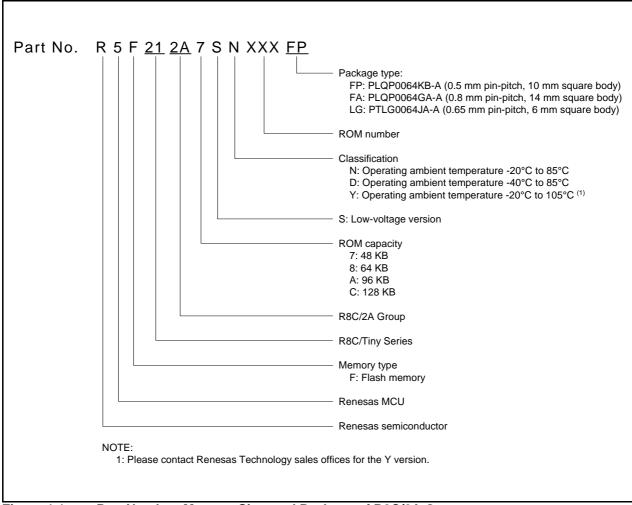


Figure 1.1 Part Number, Memory Size, and Package of R8C/2A Group

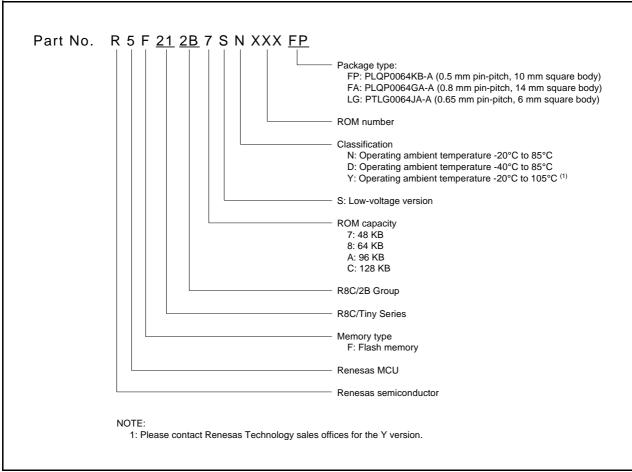


Figure 1.2 Part Number, Memory Size, and Package of R8C/2B Group

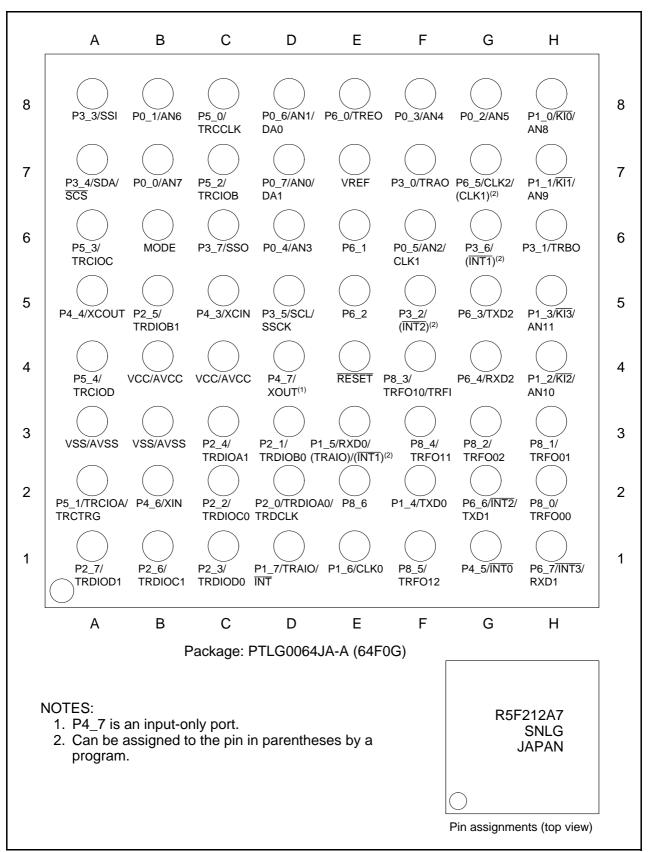


Figure 1.5 64-pin FLGA Package Pin Assignment (Top Perspective View)

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.

Interrupt are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.

The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide and assigns processor interrupt priority levels from level 0 to level 7. If a requested interrupt has higher priority than IPL, the interrupt is enabled.

2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.



3.2 R8C/2B Group

Figure 3.2 is a Memory Map of R8C/2B Group. The R8C/2B group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM area is allocated addresses 04000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.

The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.

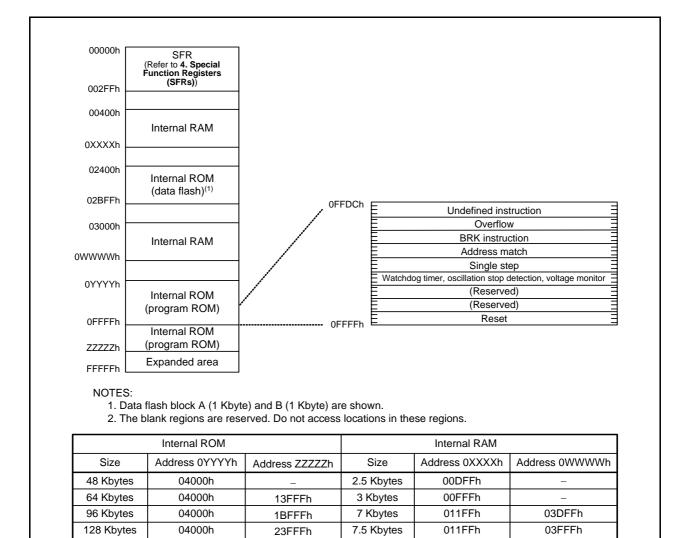


Figure 3.2 Memory Map of R8C/2B Group

SFR Information (6)⁽¹⁾ Table 4.6

Address	Register	Symbol	After reset
0140h	Timer RD Control Register 0	TRDCR0	00h
0141h	Timer RD I/O Control Register A0	TRDIORA0	10001000b
0141h	Timer RD I/O Control Register C0	TRDIORC0	10001000b
0143h	Timer RD Status Register 0	TRDSR0	110001000b
0144h	Timer RD Status Register 0 Timer RD Interrupt Enable Register 0	TRDIER0	11100000b
0145h	Timer RD PWM Mode Output Level Control Register 0	TRDPOCR0	11111000b
0146h	Timer RD Counter 0	TRD0	00h
0147h	Time ND Counter o	TROU	00h
0147H	Timer RD General Register A0	TRDGRA0	FFh
0149h	Tillier ND General Negister Au	INDONA	FFh
014Ah	Timer RD General Register B0	TRDGRB0	FFh
014Bh	Time NB General Register Bo	INDONBO	FFh
014Ch	Timer RD General Register C0	TRDGRC0	FFh
014Dh	Time NB General Register 60	INDONO	FFh
014Eh	Timer RD General Register D0	TRDGRD0	FFh
014Fh	Time NB General Register Bo	INDONDO	FFh
0150h	Timer RD Control Register 1	TRDCR1	00h
0151h	Timer RD I/O Control Register A1	TRDIORA1	10001000b
0151h	Timer RD I/O Control Register C1	TRDIORC1	10001000b
0153h	Timer RD Status Register 1	TRDSR1	110001000b
0154h	Timer RD Interrupt Enable Register 1	TRDIER1	11100000b
0155h	Timer RD PWM Mode Output Level Control Register 1	TRDPOCR1	11111000b
0156h	Timer RD Counter 1	TRD1	00h
0157h		1	00h
0158h	Timer RD General Register A1	TRDGRA1	FFh
0159h			FFh
015Ah	Timer RD General Register B1	TRDGRB1	FFh
015Bh		1	FFh
015Ch	Timer RD General Register C1	TRDGRC1	FFh
015Dh			FFh
015Eh	Timer RD General Register D1	TRDGRD1	FFh
015Fh			FFh
0160h	UART2 Transmit/Receive Mode Register	U2MR	00h
0161h	UART2 Bit Rate Register	U2BRG	XXh
0162h	UART2 Transmit Buffer Register	U2TB	XXh
0163h	,		XXh
0164h	UART2 Transmit/Receive Control Register 0	U2C0	00001000b
0165h	UART2 Transmit/Receive Control Register 1	U2C1	00000010b
0166h	UART2 Receive Buffer Register	U2RB	XXh
0167h			XXh
0168h			
0169h			
016Ah			
016Bh			
016Ch			
016Dh			
016Eh			
016Fh			
0170h			
0171h			
0172h			
0173h	_		
0174h			
0175h			
0176h			
0177h			
0178h			
0179h			_
017Ah			
017Bh			
017Ch	_		
017Dh			
017Eh			
017Fh			
-		•	•

X: Undefined
NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

SFR Information (12)⁽¹⁾ **Table 4.12**

A 1.1			A 60
Address	Register	Symbol	After reset
02C0h	A/D Register 0	AD0	XXh
02C1h			XXh
02C2h			
02C3h			
02C4h			
02C5h			
02C6h			
02C7h			
02C8h			
02C9h			
02CAh			
02CBh			
02CCh			
02CDh			
02CEh			
02CFh			
02D0h			
02D1h			
02D2h			
02D3h	A/D Control Devictor 0	ABOOMO	000040001
02D4h	A/D Control Register 2	ADCON2	00001000b
02D5h	A/D Control Deviator 0	ADCONO	000000445
02D6h	A/D Control Register 0	ADCON0	00000011b
02D7h	A/D Control Register 1	ADCON1	00h
02D8h			
02D9h			
02DAh			
02DBh			
02DCh			
02DDh			
02DEh			
02DFh			
02E0h			
02E1h			
02E2h			
02E3h	D (DOD) if D (i	220	
02E4h	Port P8 Direction Register	PD8	00h
02E5h	D + D0 D +		No.
02E6h	Port P8 Register	P8	XXh
02E7h			
02E8h			
02E9h			
02EAh			
02EBh			
02ECh			
02EDh			
02EEh			
02EFh			
02F0h			
02F1h			
02F2h			
02F3h			
02F4h			
02F5h			
02F6h			
02F7h			
02F8h			
02F9h			
02FAh			
02FBh			
02FCh	Pull-Up Control Register 2	PUR2	XXX00000b
02FDh			
02FEh			
02FFh	Timer RF Output Control Register	TRFOUT	00h
	To c. F. c. 0.1 (D.) (1050	[4] (6)
FFFFh	Option Function Select Register	OFS	(Note 2)

X: Undefined
NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. The OFS register cannot be changed by a program. Use a flash programmer to write to it.

Electrical Characteristics 5.

The electrical characteristics of N version (Topr = -20° C to 85° C) and D version (Topr = -40° C to 85° C) are listed below.

Please contact Renesas Technology sales offices for the electrical characteristics in the Y version (Topr = -20°C to 105°C).

Table 5.1 **Absolute Maximum Ratings**

Symbol	Parameter	Condition	Rated Value	Unit
Vcc/AVcc	Supply voltage		-0.3 to 6.5	V
Vı	Input voltage		-0.3 to Vcc + 0.3	V
Vo	Output voltage		-0.3 to Vcc + 0.3	V
Pd	Power dissipation	Topr = 25°C	700	mW
Topr	Operating ambient temperature		-20 to 85 (N version) / -40 to 85 (D version)	°C
Tstg	Storage temperature		-65 to 150	°C

Table 5.2	Recommended	Operating	Conditions
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Courada ad	Dorometer	Conditions	Standard			Lloit	
Symbol	Parameter		Conditions	Min.	Min. Typ. Ma		Unit
Vcc/AVcc	Supply voltage			2.2	_	5.5	V
Vss/AVss	Supply voltage			-	0	_	V
VIH	Input "H" voltage			0.8 Vcc	-	Vcc	V
VIL	Input "L" voltage			0	_	0.2 Vcc	V
IOH(sum)	Peak sum output "H" current	Sum of all pins IOH(peak)		-	=	-240	mA
IOH(sum)	Average sum output "H" current	Sum of all pins IOH(avg)		_	-	-120	mA
IOH(peak)	Peak output "H"	Except P2_0 to P2_7		-	-	-10	mA
	current	P2_0 to P2_7		=	=	-40	mA
IOH(avg)	Average output	Except P2_0 to P2_7		-	=	-5	mA
	"H" current	P2_0 to P2_7		-	-	-20	mA
IOL(sum)	Peak sum output "L" current	Sum of all pins IOL(peak)		-	=	240	mA
IOL(sum)	Average sum output "L" current	Sum of all pins IOL(avg)		=	=	120	mA
IOL(peak)	Peak output "L"	Except P2_0 to P2_7		-	_	10	mA
	current	P2_0 to P2_7		-	-	40	mA
IOL(avg)	Average output	Except P2_0 to P2_7		-	=	5	mA
	"L" current	P2_0 to P2_7		-	-	20	mA
f(XIN)	XIN clock input osc	cillation frequency	3.0 V ≤ Vcc ≤ 5.5 V	0	-	20	MHz
			2.7 V ≤ Vcc < 3.0 V	0	-	10	MHz
			2.2 V ≤ Vcc < 2.7 V	0	-	5	MHz
f(XCIN)	XCIN clock input o	scillation frequency	2.2 V ≤ Vcc ≤ 5.5 V	0	-	70	kHz
=	System clock	OCD2 = 0	3.0 V ≤ Vcc ≤ 5.5 V	0	=	20	MHz
		XIN clock selected	2.7 V ≤ Vcc < 3.0 V	0	=	10	MHz
			2.2 V ≤ Vcc < 2.7 V	0	_	5	MHz
		OCD2 = 1 On-chip oscillator clock selected	FRA01 = 0 Low-speed on-chip oscillator clock selected	-	125	-	kHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 3.0 V ≤ Vcc ≤ 5.5 V	_	-	20	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 2.7 V ≤ Vcc ≤ 5.5 V	_	-	10	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 2.2 V ≤ Vcc ≤ 5.5 V	-	-	5	MHz

- 1. VCC = 2.2 to 5.5 V at $T_{OPT} = -20$ to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
- 2. The average output current indicates the average value of current measured during 100 ms.

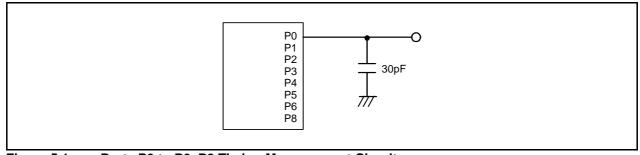


Figure 5.1 Ports P0 to P6, P8 Timing Measurement Circuit

Table 5.3 A/D Converter Characteristics(1)

Cumbal	Parameter	Conditions	Standard			Unit	
Symbol	Farameter		Conditions	Min.	Тур.	Max.	Offic
_	Resolution		Vref = AVCC	_	-	10	Bit
=	Absolute	10-bit mode	φAD = 10 MHz, Vref = AVCC = 5.0 V	_	-	±3	LSB
	accuracy	8-bit mode	φAD = 10 MHz, Vref = AVCC = 5.0 V	_	-	±2	LSB
		10-bit mode	φAD = 10 MHz, Vref = AVCC = 3.3 V	_	-	±5	LSB
		8-bit mode	φAD = 10 MHz, Vref = AVCC = 3.3 V	_	-	±2	LSB
		10-bit mode	φAD = 5 MHz, Vref = AVCC = 2.2 V	_	-	±5	LSB
		8-bit mode	φAD = 5 MHz, Vref = AVCC = 2.2 V	_	-	±2	LSB
Rladder	Resistor ladder		Vref = AVCC	10	=	40	kΩ
tconv	Conversion time	10-bit mode	φAD = 10 MHz, Vref = AVCC = 5.0 V	3.3	-	-	μS
	8-bit mode	φAD = 10 MHz, Vref = AVCC = 5.0 V	2.8	-	-	μS	
Vref	Reference voltag	e		2.2	-	AVcc	V
VIA	Analog input volta	age ⁽²⁾		0	-	AVcc	V
-	A/D operating	Without sample and hold	Vref = AVCC = 2.7 to 5.5 V	0.25	_	10	MHz
	clock frequency	With sample and hold	Vref = AVCC = 2.7 to 5.5 V	1	-	10	MHz
		Without sample and hold	Vref = AVCC = 2.2 to 5.5 V	0.25	-	5	MHz
		With sample and hold	Vref = AVCC = 2.2 to 5.5 V	1	-	5	MHz

- Vcc/AVcc = Vref = 2.2 to 5.5 V at Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
 When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.4 D/A Converter Characteristics(1)

Symbol	Parameter	Conditions	Standard			Unit
Symbol	Falameter	Conditions	Min.	Тур.	Max.	Offic
_	Resolution		_	-	8	Bit
_	Absolute accuracy		_	-	1.0	%
tsu	Setup time		_	-	3	μS
Ro	Output resistor		4	10	20	kΩ
lVref	Reference power input current	(NOTE 2)	-	_	1.5	mA

- 1. Vcc/AVcc = Vref = 2.7 to 5.5 V at Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
- 2. This applies when one D/A converter is used and the value of the DAi register (i = 0 or 1) for the unused D/A converter is 00h. The resistor ladder of the A/D converter is not included. Also, even if the VCUT bit in the ADCON1 register is set to 0 (VREF not connected), Ivref flows into the D/A converters.

Table 5.6 Flash Memory (Data flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions		Unit		
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
_	Program/erase endurance ⁽²⁾		10,000(3)	-	-	times
_	Byte program time (program/erase endurance ≤ 1,000 times)		-	50	400	μS
_	Byte program time (program/erase endurance > 1,000 times)		-	65	_	μS
_	Block erase time (program/erase endurance ≤ 1,000 times)		-	0.2	9	S
_	Block erase time (program/erase endurance > 1,000 times)		=	0.3	-	S
td(SR-SUS)	Time delay from suspend request until suspend		=	-	97+CPU clock × 6 cycles	μS
_	Interval from erase start/restart until following suspend request		650	-	_	μS
_	Interval from program start/restart until following suspend request		0	-	-	ns
_	Time from suspend until program/erase restart		-	-	3+CPU clock × 4 cycles	μS
_	Program, erase voltage		2.7	_	5.5	V
_	Read voltage		2.2	_	5.5	V
=	Program, erase temperature		-20(8)	-	85	°C
_	Data hold time ⁽⁹⁾	Ambient temperature = 55 °C	20	_	-	year

- 1. Vcc = 2.7 to 5.5 V at Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
- 2. Definition of programming/erasure endurance
 - The programming and erasure endurance is defined on a per-block basis.

If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.

However, the same address must not be programmed more than once per erase operation (overwriting prohibited).

- 3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
- 4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
- 5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
- 6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
- 7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
- 8. -40°C for D version.
- 9. The data hold time includes time that the power supply is off or the clock is not supplied.

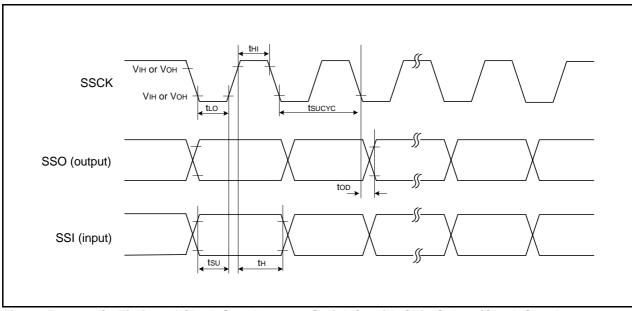


Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.15 Timing Requirements of I²C bus Interface (1)

Symbol	Parameter	Condition	Standard			Unit
Symbol	Parameter		Min.	Тур.	Max.	Unit
tscl	SCL input cycle time		12tcyc + 600 ⁽²⁾	_	-	ns
tsclh	SCL input "H" width		3tcyc + 300 ⁽²⁾	=	-	ns
tscll	SCL input "L" width		5tcyc + 500 ⁽²⁾	=	-	ns
t sf	SCL, SDA input fall time		=	=	300	ns
tsp	SCL, SDA input spike pulse rejection time		-	-	1tcyc ⁽²⁾	ns
tBUF	SDA input bus-free time		5tcyc(2)	=	-	ns
tstah	Start condition input hold time		3tcyc ⁽²⁾	=	-	ns
tstas	Retransmit start condition input setup time		3tcyc(2)	=	=	ns
tstop	Stop condition input setup time		3tcyc ⁽²⁾	=	=	ns
tsdas	Data input setup time		1tcyc + 20 ⁽²⁾	=	-	ns
tsdah	Data input hold time		0	=	-	ns

- 1. Vcc = 2.2 to 5.5 V, Vss = 0 V and Topr = -20 to $85^{\circ}C$ (N version) / -40 to $85^{\circ}C$ (D version), unless otherwise specified.
- 2. 1tcyc = 1/f1(s)

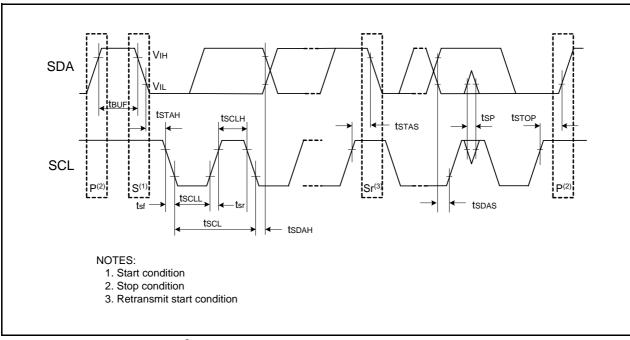


Figure 5.7 I/O Timing of I²C bus Interface

Table 5.16 Electrical Characteristics (1) [Vcc = 5 V]

Symbol	Parameter	Condition		Standard			Unit	
Symbol	Parameter			Min.	Тур.	Max.	Unit	
Vон	Output "H" voltage	Except P2_0 to P2_7, XOUT	Iон = -5 mA		Vcc - 2.0	_	Vcc	V
			IOH = -200 μA		Vcc - 0.5	-	Vcc	V
		P2_0 to P2_7	Drive capacity HIGH	Iон = -20 mA	Vcc - 2.0	_	Vcc	V
			Drive capacity LOW	Iон = -5 mA	Vcc - 2.0	_	Vcc	V
		XOUT	Drive capacity HIGH	Iон = -1 mA	Vcc - 2.0	_	Vcc	V
			Drive capacity LOW	IOH = -500 μA	Vcc - 2.0	_	Vcc	V
Vol	Output "L" voltage	voltage Except P2_0 to P2_7, XOUT	IoL = 5 mA		-	_	2.0	V
			IoL = 200 μA		-	_	0.45	V
		P2_0 to P2_7	Drive capacity HIGH	IoL = 20 mA	-	_	2.0	V
			Drive capacity LOW	IoL = 5 mA	-	_	2.0	V
		XOUT	Drive capacity HIGH	IoL = 1 mA	-	_	2.0	V
			Drive capacity LOW	IoL = 500 μA	-	_	2.0	V
VT+-VT-	Hysteresis	INTO, INT1, INT2, INT3, KI0, KI1, KI2, KI3, TRAIO, TRFI, RXD0, RXD1, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.1	0.5	_	V
		RESET			0.1	1.0	-	V
Іін	Input "H" current		VI = 5 V		_	_	5.0	μΑ
lıL	Input "L" current		VI = 0 V		_	_	-5.0	μΑ
RPULLUP	Pull-up resistance		VI = 0 V		30	50	167	kΩ
RfXIN	Feedback resistance	XIN			-	1.0	_	ΜΩ
RfXCIN	Feedback resistance	XCIN			=	18	-	МΩ
VRAM	RAM hold voltage	•	During stop mode		1.8	-	_	V

^{1.} Vcc = 4.2 to 5.5 V at Topr = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.28 Serial Interface	erface
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Symbol	Parameter		Standard		
			Max.	Unit	
tc(CK)	CLKi input cycle time		=	ns	
tW(CKH)	CLKi input "H" width		-	ns	
tW(CKL)	CLKi Input "L" width		-	ns	
td(C-Q)	TXDi output delay time		80	ns	
th(C-Q)	TXDi hold time		-	ns	
tsu(D-C)	RXDi input setup time		-	ns	
th(C-D)	RXDi input hold time		-	ns	

i = 0 to 2

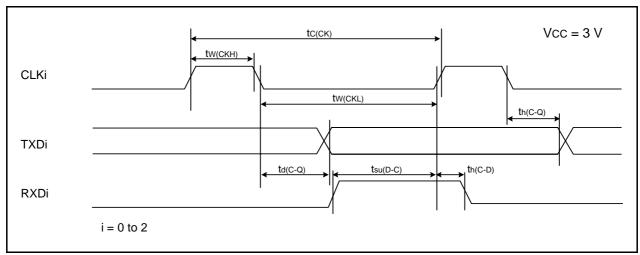


Figure 5.16 Serial Interface Timing Diagram when Vcc = 3 V

Table 5.29 External Interrupt $\overline{\text{INTi}}$ (i = 0, 2, 3) Input

Symbol	Parameter	Stan	Unit	
Symbol	Falanielei			Max.
tW(INH)	INTO input "H" width		-	ns
tW(INL)	ĪNT0 input "L" width		_	ns

- 1. When selecting the digital filter by the $\overline{\text{INTi}}$ input filter select bit, use an $\overline{\text{INTi}}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
- 2. When selecting the digital filter by the $\overline{\text{INTi}}$ input filter select bit, use an $\overline{\text{INTi}}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

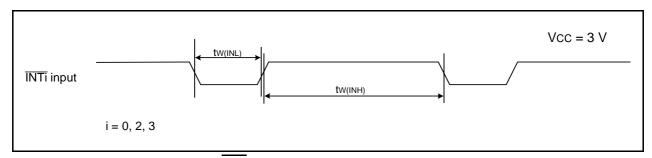


Figure 5.17 External Interrupt INTi Input Timing Diagram when Vcc = 3 V

Timing requirements

(Unless Otherwise Specified: Vcc = 2.2 V, Vss = 0 V at Topr = 25°C) [Vcc = 2.2 V]

Table 5.32 XIN Input, XCIN Input

Symbol	Parameter		Standard		
			Max.	Unit	
tc(XIN)	XIN input cycle time		-	ns	
twh(xin)	XIN input "H" width		-	ns	
tWL(XIN)	XIN input "L" width		-	ns	
tc(XCIN)	XCIN input cycle time		-	μS	
twh(xcin)	XCIN input "H" width		=	μS	
twl(xcin)	XCIN input "L" width		-	μS	

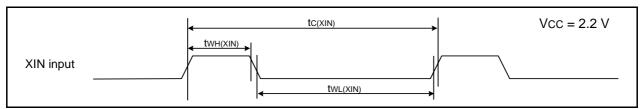


Figure 5.18 XIN Input and XCIN Input Timing Diagram when Vcc = 2.2 V

Table 5.33 TRAIO Input, INT1 Input

Symbol	Parameter		Standard		
Symbol			Max.	Unit	
tc(TRAIO)	TRAIO input cycle time	TBD	-	ns	
twh(traio)	TRAIO input "H" width	TBD	=	ns	
tWL(TRAIO)	TRAIO input "L" width	TBD	-	ns	



Figure 5.19 TRAIO Input and $\overline{\text{INT1}}$ Input Timing Diagram when Vcc = 2.2 V

Table 5.34 TRFI Input

Symbol	Parameter	Stan	Unit		
Symbol	Faianietei		Max.	Offic	
tc(TRFI)	TRFI input cycle time		-	ns	
twh(TRFI)	TRFI input "H" width		-	ns	
twl(TRFI)	TRFI input "L" width		-	ns	

- 1. When using timer RF input capture mode, adjust the cycle time to (1/timer RF count source frequency × 3) or above.
- 2. When using timer RF input capture mode, adjust the pulse width to (1/timer RF count source frequency × 1.5) or above.

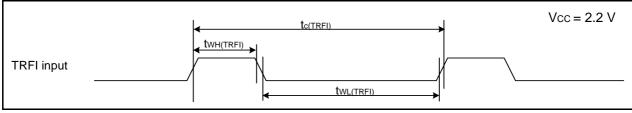
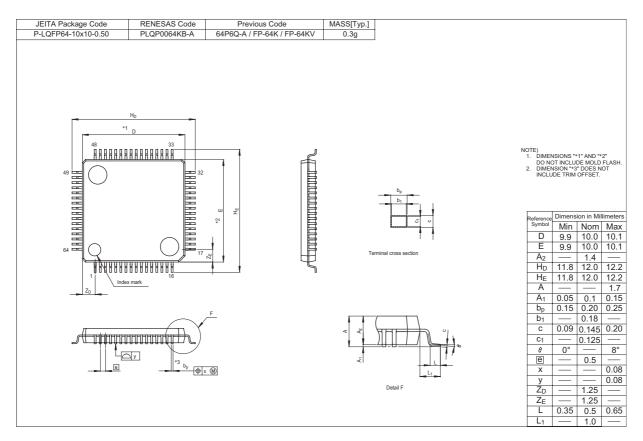
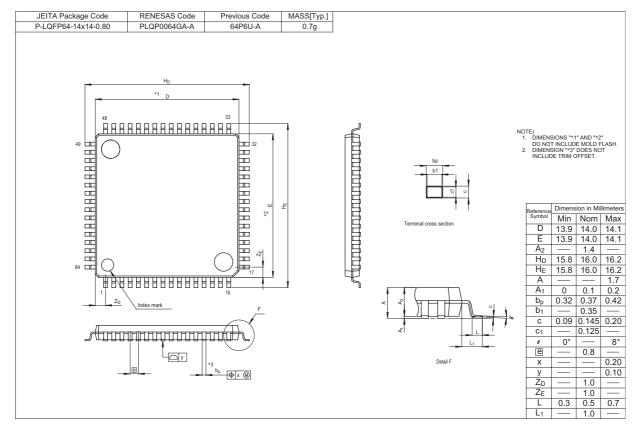


Figure 5.20 TRFI Input Timing Diagram when Vcc = 2.2 V

Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the "Packages" section of the Renesas Technology website.





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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510